

IIA SB4 – Fundamentals of Integrated Photonics

Prof. Qixiang Cheng, Dr. Chunhui Yao

Centre for Photonic Systems Engineering Department Electrical Engineering Division

Outline

- 1. Background Introduction
- 2. Fundamentals of Integrated Photonics
- 3. Derivation of Optical Waveguide Modes
- 4. Coupling Between Waveguides
- 5. Mode Simulation and Case Analysis



Development of optical communication

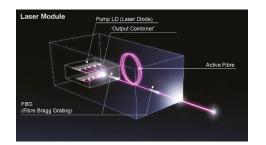
Theoretical Foundation

• In 1966, Charles K. Kao (Nobel Prize in Physics 2009) proposed the concept that light could be guided in dielectric fibers — paving the way for modern optical communication.

Key Enabling Technologies

- Lasers: Invention of the III-V laser (first in 1960) and subsequent rapid development provided coherent light sources for optical links.
- **Low-loss optical fibers**: Key breakthroughs in reducing attenuation (1970s) made long-distance fiber transmission feasible.
- **Dense Wavelength Division Multiplexing (DWDM)**: Enables multiple channels to transmit simultaneously through a single fiber, allowing massive bandwidth scaling.
- Optical Amplifiers (e.g., Erbium-Doped Fiber Amplifiers, EDFAs): Boost optical signals directly without electrical conversion, enabling long-haul transmission across global networks.





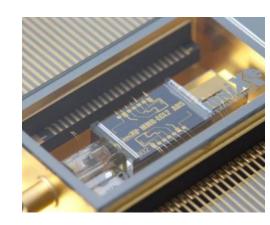




From Optical Fibers to Integrated Photonics

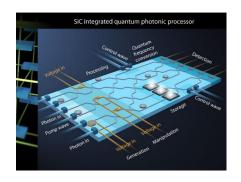
Rise of Silicon Photonics:

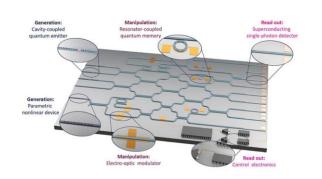
- With advances in nanofabrication technologies, the functionalities of traditional fiber-based systems can now be integrated onto a **single photonic chip**.
- This marks a paradigm shift from bulky **fiber-based optics** to **on-chip integration**, enabling scalable, stable, and manufacturable photonic systems.

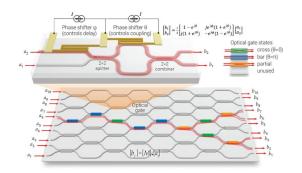


Key features:

- Integrated Photonic Circuits (PICs) manipulate light on a chip, similar to how electronic ICs control electrons.
- Fabricated via CMOS-compatible techniques (e.g., DUV lithography) on various material platforms, such as Si, SiN, and InP,
- Typical components include waveguides, couplers, resonators, lasers, modulators, detectors...







Compact, low-cost, largebandwidth, power-efficient, and etc.



Underlying Driving force — Rapid Growth of Data Traffic

Global internet traffic is **growing exponentially**, driven by:

- Mobile internet, streaming video and real-time communications
- Al model training and edge computing
- Cloud services and IoT devices

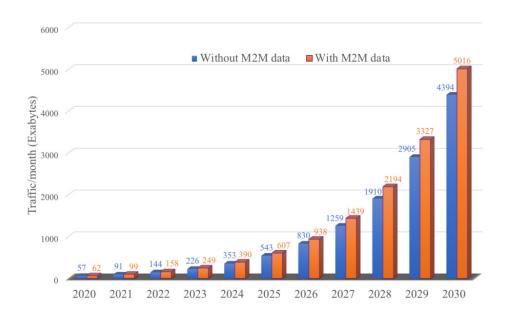
We Live in a World of Data



Data Needs to be Accessible Always and in Real-Time

This impose great performance pressure on data centers:

- Ultra-high bandwidth of >1 Tbps
- Low communication latency <1 μs
- Target energy consumption is <1 pJ/bit

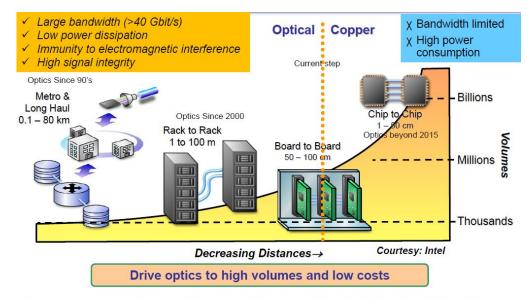




Electrical vs Optical Interconnects in Data Centers

Yet, electrical links (e.g., copper wires, electronic chips) face:

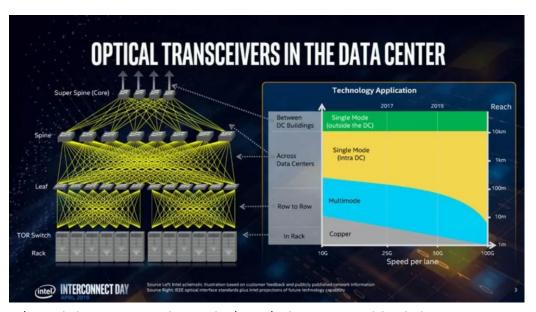
- Bandwidth limitations due to RC delay and skin effect
- High power consumption and complex heat management
- EMI (electromagnetic interference) sensitivity



Optics has progressively eliminated copper in the metro and long haul network in the last 20 years and will continue its migration all the way to chip to chip application in the next 10 years.

In contrast, optical interconnects offer:

- Much larger bandwidth (via multiplexing technologies)
- Much lower power consumption
- Low latency, with immunity to EMI



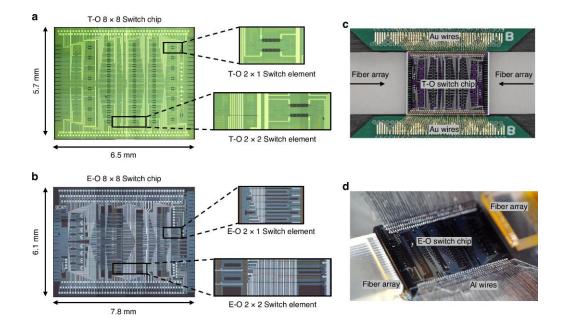
Photonic interconnects increasingly replacing copper wiring in interconnects

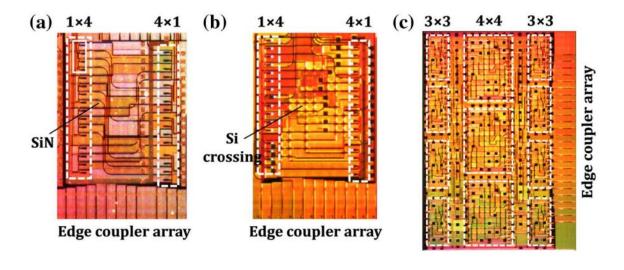


Integrated Photonics for Optical Interconnect/Switching

Integrated optical switches empowering next-generation optical interconnection/switching:

- Enable compact, scalable optical interconnects and on-chip switching
- Supports high-throughput, low-latency communication for AI and HPC systems
- Largely adopted by leading companies, such as Google, Meta, Amazon, Alibaba Cloud...





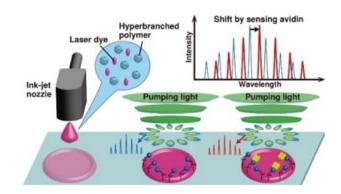
Broad Application Perspectives

Optical Interconnect



- Data centers and supercomputers
- Optical I/O and all-optical transmission
- Chip-to-chip optical communication
- 5G/6G fronthaul optical networks
- All-optical metro and access networks

Optical sensing



- Integrated spectroemter for biomedical, indusctral spectrosopic applications
- Portable/wearable sensing devices
- Hyperspectral imaging
- Optical coherence tomography (OCT)

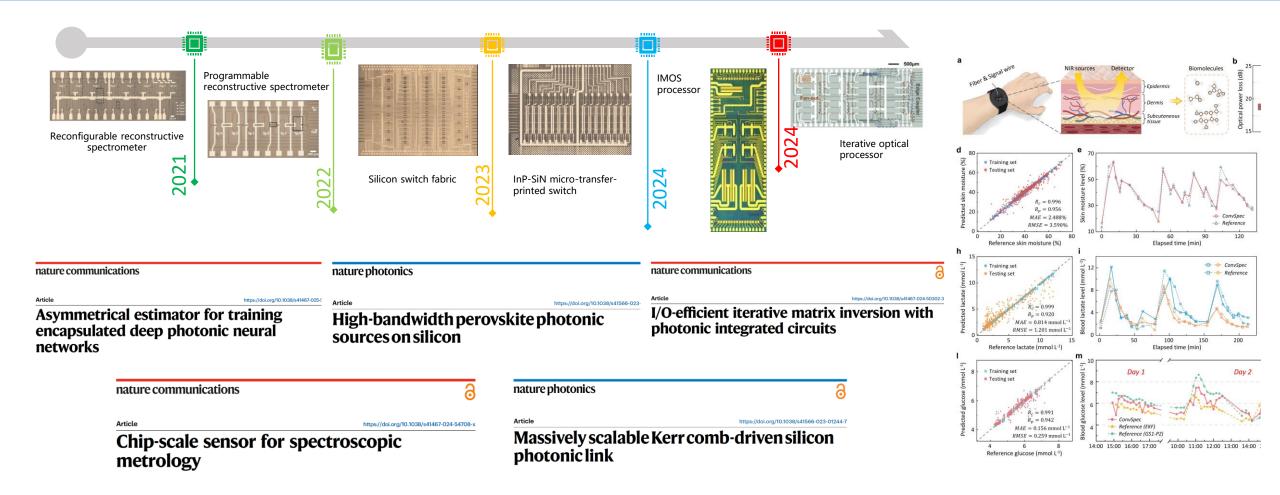
Optical computing



- Al acceleration photonic chips
- 5G/6G BBU signal processing
- Quantum computing processors
- Linear optical computing chips
- Reconfigurable photonic processors



Recent Progresses





Advances in Photonic Integration Technologies

Technology Trends

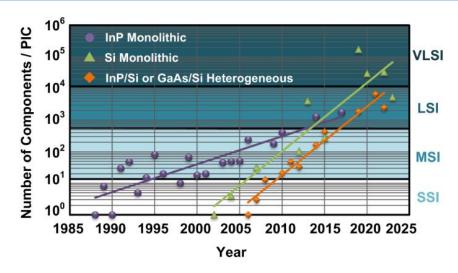
- Rapid scaling in photonic integration: From a few components per chip in the 1990s to
 >10⁵ components per PIC today (approaching VLSI level)
- Transition from monolithic to heterogeneous integration: Combining Si, SiN, and, InP on a single chip platform via wafer-scale processes
- Leveraging CMOS-compatible lithography (193nm DUV) and wafer-level packaging

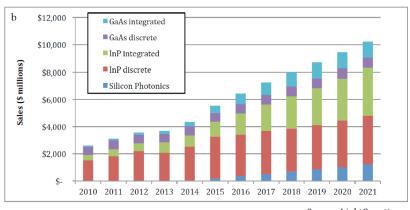
Market Growth

Strong year-over-year growth in the optical transceiver market → Dominated by
 Silicon Photonics and InP integrated platforms

Current Challenges

- Lack of industry-wide standardization for PIC design (no "Moore's Law" equivalent)
- Absence of low-cost on-chip light sources (especially integrated lasers on Si platforms)
- Difficulties in precise alignment between optical and electronic domains





Source: LightCounting



SB4: Weekly Plan

Weekly Plan:

Week 1: Introduce fundamental photonics theory and basic waveguide simulation with Lumerical software, focusing on understanding and setting up simple models.

Week 2: Dive into eigenmode analysis in silicon waveguides using both theoretical calculations and Lumerical FDTD. Design and simulate a single-mode waveguide, observe the mode propagation, and compare it with the calculated single-mode condition.

Week 3: Design and simulate waveguide photonic components — i.e., a directional coupler. Calculate their key structural parameters using theoretical models and simulate both components with Lumerical FDTD.

Week 4: Validate simulation results by comparing them with theoretical and numerical models, optimize their performance, ensuring accuracy and reliability of the simulations.

Coursework:

| Coursework | Due date | Marks |
|----------------------|--------------------------|-------|
| Interim report 1 | 23 rd of May | 20 |
| Interim report 2 | 3 rd of June | 20 |
| Final summary report | 12 th of June | 40 |

^{* 100%} of the marks will be given based on individual performance.



SB4: Schedule

Compulsory sessions:

| Week | Day | Date | Time | Location |
|------|---------|--------------------------|--------------------|-------------------------|
| 1 | Friday | 16 th of May | 9:00 am – 11:00 am | CGC Seminar room |
| 1 | Tuesday | 20 th of May | 11:00 am – 1:00 pm | CGC Seminar room |
| 2 | Friday | 23 rd of May | 9:00 am – 11:00 am | EED Seminar room |
| 2 | Tuesday | 27 th of May | 11:00 am – 1:00 pm | CGC Seminar room |
| 3 | Friday | 30 th of May | 9:00 am – 11:00 am | EED Seminar room |
| 3 | Tuesday | 3 rd of June | 11:00 am – 1:00 pm | CGC Seminar room |
| 4 | Friday | 6 th of June | 9:00 am – 11:00 am | CGC Seminar room |
| 4 | Tuesday | 10 th of June | 11:00 am – 1:00 pm | CGC Seminar room |



^{*} Not having optional sessions as we have no need to stay in the lab and you can do your simulations anywhere

Fabrication Processes of Integrated Photonic Chips

Using a passive **Silicon-on-Isolator (SOI) platform** as example:

1. Typical SOI wafer stack:

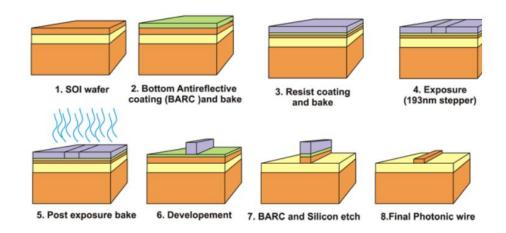
- Top: 220 nm Silicon layer (waveguide layer)
- Middle: 2 μm **Silicon dioxide** (buried oxide, BOX) layer
- Bottom: **Silicon** substrate

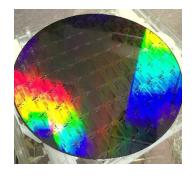
2. Lithography & Etching:

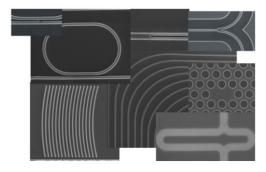
- Spin-coat photoresist and apply anti-reflective coating
- Use deep UV (DUV) exposure to transfer patterns
- Develop resist and perform reactive ion etching to define structures

3. Post-processing & Packaging

- Deposit upper cladding for protection (typically SiO₂ or polymer)
- Add metal pads or electrothermal heaters for electrical control
- Dice the chip, and polish facets or fabricate grating couplers for fiber interface



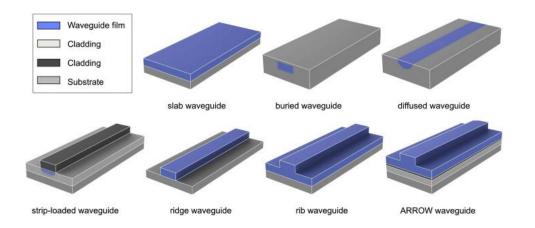






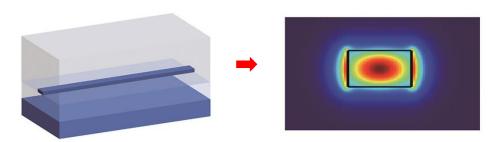
Integrated Optical Waveguide

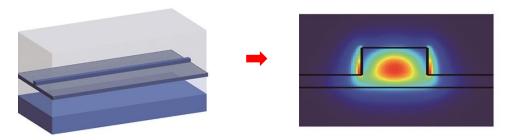
Optical waveguide – the most fundamental element in integrated photonics, guiding the propagation of light (like optical fibers)



- Slab (Planar) Waveguide: Index contrast (confinement) in one dimension
- Strip/Ridge/Wire (rectangle) Waveguide: Index contrast (confinement)
 in two dimensions
- **Rib waveguide, Slot waveguide and etc.**: more complex index confinement.

Waveguide Mode – the spatial distribution of optical energy within the waveguide







Fundamentals of Electromagnetic waves

Maxwell's Equations — describe how electric fields (E/D) and magnetic fields (B/H) are generated and interact

| Name | Differential form | Integral form |
|--|--|--|
| Gauss's law | $\nabla \cdot \mathbf{E} = \frac{\rho}{\varepsilon_0}$ | $ \oint \int_{\partial V} \mathbf{E} \cdot d\mathbf{A} = \frac{Q(V)}{\varepsilon_0} $ |
| Gauss's law for magnetism | $\nabla \cdot \mathbf{B} = 0$ | $\iint_{\partial V} \mathbf{B} \cdot d\mathbf{A} = 0$ |
| Maxwell-Faraday equation (Faraday's law of induction) | $\nabla \times \mathbf{E} = -\frac{\partial \mathbf{B}}{\partial t}$ | $\oint_{\partial S} \mathbf{E} \cdot \mathbf{dl} = -\frac{\partial \Phi_{B,S}}{\partial t}$ |
| Ampère's circuital law (with Maxwell's correction) | $\nabla \times \mathbf{B} = \mu_0 \mathbf{J} + \mu_0 \varepsilon_0 \frac{\partial \mathbf{E}}{\partial t}$ | $\oint_{\partial S} \mathbf{B} \cdot d\mathbf{l} = \mu_0 I_S + \mu_0 \varepsilon_0 \frac{\partial \Phi_{E,S}}{\partial t}$ |

$$D = \varepsilon E$$
 $B = \mu H$ $J = \sigma E$

Form the foundation for deriving wave propagation, light behavior, and mode formation in optical waveguides

Monochromatic Assumption (i.e. for a specific frequency ω)

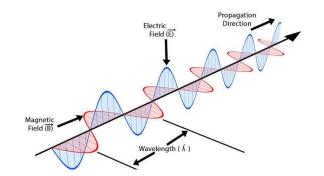
$$\mathbf{E}(r,t) = \mathbf{E}(r)e^{i\omega t}, \quad \mathbf{H}(r,t) = \mathbf{H}(r)e^{i\omega t}$$

Maxwell's wave equation (Helmholtz equation):

$$abla^2\mathbf{E}(r)+k^2n^2(r)\mathbf{E}(r)=0$$

$$\nabla^2 \mathbf{H}(r) + k^2 n^2(r) \mathbf{H}(r) = 0$$

In free space (uniform media), electromagnetic waves are perfectly transverse: i.e. the electric field (E) and magnetic field (H) oscillate **perpendicularly** to each other and to the direction of propagation.



TEM (Transverse Electric and Magnetic) wave



Three-Layer Planar Waveguide (index contrast in x direction):

Maxwell's wave equation (Helmholtz equation):

$$\nabla^2 \boldsymbol{E}(\boldsymbol{r}) + k^2 n^2 (\boldsymbol{r}) \boldsymbol{E}(\boldsymbol{r}) = 0$$
 (1.1)

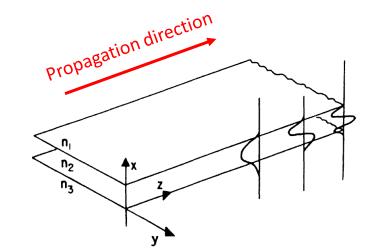
where

E: the electric field vector

r: the position vector, i.e. r(x, y, z)

 $\boldsymbol{n}(\boldsymbol{r})$: the index of refraction

 $k \equiv \omega/c$: the free-space wavenumber



$$x = -t_9 \frac{n_2}{n_3}$$

Uniform plane wave propagating in the z direction; however, the index contrast in the x direction prevents maintaining a pure TEM mode, leading to **TE** (**Transverse Electric**) and **TM** (**Transverse Magnetic**) modes.

As for TE modes, where E(z) = 0, the monochromatic assumption becomes:

 $E(r) = E(x, y) \exp(-i\beta z)$ where β is the propagation constant, $\beta = kn_{eff} = \omega n_{eff}/c$ (1.2)

Substituting (1.2) into (1.1), the wave equation becomes:

$$\partial^{2} \boldsymbol{E}(x,y) / \partial x^{2} + \partial^{2} \boldsymbol{E}(x,y) / \partial y^{2} + \left[k^{2} n^{2} (\boldsymbol{r}) - \beta^{2} \right] \boldsymbol{E}(x,y) = 0$$
 (1.3)

Since the waveguide is assumed infinite in the y direction, (1.3) can be rewritten separately for the three regions in x:

Region 1
$$\partial^2 E(x,y)/\partial x^2 + \left[k^2 n_1^2 - \beta^2\right] E(x,y) = 0$$

Region 2 $\partial^2 E(x,y)/\partial x^2 + \left[k^2 n_2^2 - \beta^2\right] E(x,y) = 0$ (1.4)
Region 3 $\partial^2 E(x,y)/\partial x^2 + \left[k^2 n_3^2 - \beta^2\right] E(x,y) = 0$

The solutions of (1.4) are either sinusoidal or exponential functions of x in each of the regions, depending on whether $(k^2n^2_i - \beta^2)$, i = 1, 2, 3 is greater or less than zero.

Therefore, the transverse function $E_{\nu}(x)$ has the general form:

Region 1
$$\partial^2 E(x,y)/\partial x^2 + \left[k^2 n_1^2 - \beta^2\right] E(x,y) = 0$$

Region 2 $\partial^2 E(x,y)/\partial x^2 + \left[k^2 n_2^2 - \beta^2\right] E(x,y) = 0$ $\longrightarrow E_y(x) = \begin{cases} A \exp(-qx) & 0 \le x \le \infty \\ B \cos(hx) + C \sin(hx) & -t_g \le x \le 0 \end{cases}$ (1.5)
Region 3 $\partial^2 E(x,y)/\partial x^2 + \left[k^2 n_3^2 - \beta^2\right] E(x,y) = 0$ $\longrightarrow E_y(x) = \begin{cases} A \exp(-qx) & 0 \le x \le \infty \\ B \cos(hx) + C \sin(hx) & -t_g \le x \le 0 \end{cases}$ (1.5)

where A, B, C, D, q, h, and p are all constants that can be determined by matching the boundary conditions.

Boundary conditions:

At refractive index interfaces, the **tangential components** of both electric field and magnetic field (corresponding to the derivative of electric field) **must be continuous**, in order to avoid unphysical discontinuities (e.g. infinite surface current).

i.e. $E_{\nu}(x)$ and $\partial E_{\nu}(x)/\partial x$ must be continuous at the interfaces (x=0, and $x=-t_g$)



Then, the transverse function $E_{\nu}(x)$ can be expressed in terms of a single constant C', as:

$$E_{y}(x) = \begin{cases} C' \exp(-qx) & 0 \le x \le \infty \\ C' \left[\cos(hx) - (q/h)\sin(hx)\right] & -t_{g} \le x \le 0 \\ C' \left[\cos(ht_{g}) + (q/h)\sin(ht_{g})\right] \exp\left[p(x + t_{g})\right] & -\infty \le x \le -t_{g} \end{cases}$$
(1.6)

Substituting (1.6) into (1.3), we get:

$$q = (\beta^{2} - n_{1}^{2}k^{2})^{1/2}, \qquad h = (n_{2}^{2}k^{2} - \beta^{2})^{1/2},$$

$$p = (\beta^{2} - n_{3}^{2}k^{2})^{1/2}, \qquad k \equiv \omega/c.$$
(1.7)

As $\partial E_{\nu}(x)/\partial x$ continuous at n_2 - n_3 boundary (i.e. $x=-t_g$), then:

$$-h\sin\left(-ht_{g}\right) - h\left(q/h\right)\cos\left(-ht_{g}\right) = p\left[\cos\left(ht_{g}\right) + \left(q/h\right)\sin\left(ht_{g}\right)\right] \qquad \text{or} \qquad \tan\left(ht_{g}\right) = \frac{p+q}{h\left(1-pq/h^{2}\right)} \tag{1.8}$$

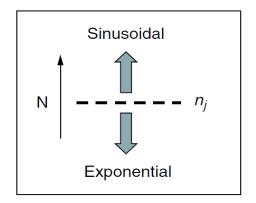
Leads to discrete values of $\beta \Rightarrow \beta_m \ (q_m, h_m \text{ and } p_m)$

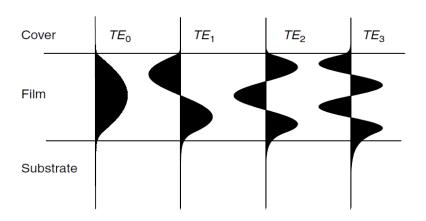
• Solutions for β_m can be obtained graphically or computed numerically using software tools.



TE Mode Profiles:

- In the core region (higher refractive index), the optical field oscillates sinusoidally.
 - The number of field nodes defines the mode order:
 - The TE_0 mode, with no internal nodes, is called the **fundamental mode**.
 - Higher-order modes (e.g., TE_1 , TE_2 , and TE_3) have one, two, three, or more nodes, respectively.
- In other regions (lower refractive index), the field decays exponentially, called the evanescent field/tail.







In analog, for **TM Modes** (i.e., H(z) = 0), we have:

$$H_{y}(x,z,t) = H_{y}(x)e^{i(\omega t - \beta z)} \qquad E_{x}(x,z,t) = \frac{i}{\omega \varepsilon} \frac{\partial H_{y}}{\partial z} = \frac{\beta}{\omega \varepsilon} H_{y}(x)e^{i(\omega t - \beta z)} \qquad E_{z}(x,z,t) = -\frac{i}{\omega \varepsilon} \frac{\partial H_{y}}{\partial x}$$

These equations yield:

$$H_{y}(x) = \begin{cases} -C' \left[\frac{h}{\overline{q}} \cos(ht_{g}) + \sin(ht_{g}) \right] \exp\left[p(x + t_{g}) \right] & -\infty \le x \le -t_{g} \\ C' \left[-\frac{h}{\overline{q}} \cos(hx) + \sin(hx) \right] & -t_{g} \le x \le 0 \end{cases}$$

$$C' - \frac{h}{\overline{q}} \exp(-qx) \qquad 0 \le x \le \infty$$

Boundary condition: $\partial H_y/\partial x$ is continuous at the n_2 - n_3 boundary



$$\tan\left(ht_g\right) = \frac{h(\overline{p} + \overline{q})}{h^2 - \overline{p}\overline{q}}$$

To summarize, the **non-zero field components**:

TE Modes: E_y , H_x , H_z (minor); **TM Modes:** H_y , E_x , E_z (minor);

Cutoff Condition

The **cutoff condition** represents the point at which the field becomes oscillatory in *Regions 1* and *3*, i.e., when the mode can no longer be well confined within the waveguide.

For symmetrical planar waveguide (i.e. $n_1 = n_3$) at cutoff condition, the magnitude of β is given by (see Eq. 1.7):

$$\beta = kn_1 = kn_3
k = \omega / c = 2\pi / \lambda_0$$

$$p = q = 0
h = k (n_2^2 - n_1^2)^{1/2} = k (n_2^2 - n_3^2)^{1/2}$$

For waveguiding of a given mode to occur, one must have (see Eq. 1.8):

$$tan(ht_g) = \frac{p+q}{h(1-pq/h^2)} = 0$$
 \rightarrow $ht_g = m_s \pi, \ m_s = 0,1,2,3,...$

$$\Delta n = (n_2 - n_1) > \frac{m_s^2 \lambda_0^2}{4t_g^2 (n_2 + n_1)}, \quad m_s = 0, 1, 2, 3, \dots$$
 (1.9)

The cutoff condition given in (1.9) determines which modes can be supported by a waveguide with a given Δn and ratio of $\lambda o/t_g$.



The lowest mode $m_s = 0$

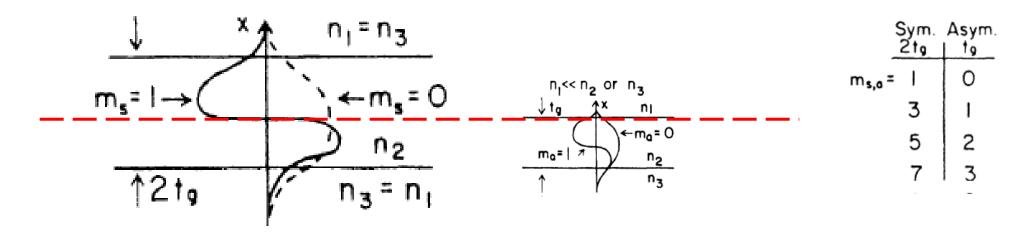
- Δn>0 ⇒ any wavelength could be guided in this mode
- small Δn and/or large $\lambda_0/t_g \Rightarrow$ poor confinement \Rightarrow large evanescent tails

Cutoff Condition

For asymmetrical planar waveguide (e.g., $n_2 > n_3 > n_1$), the cutoff condition becomes:

$$\Delta n = (n_2 - n_3) > \frac{(2m_a + 1)\lambda_0^2}{16(n_2 + n_3)t_g^2} = \frac{m_s^2 \lambda_0^2}{4(n_2 + n_3)(2t_g)^2}, \quad m_s = (2m_a + 1), \quad m_a = 0,1,2,3,... \quad (1.10)$$

By comparing Eq. 1.9 & 1.10, it can be seen that the asymmetric waveguide supports only modes are similar/correspond to the odd modes of a symmetric waveguide of twice its thickness.



Modes in a Strip (rectangular) Waveguide

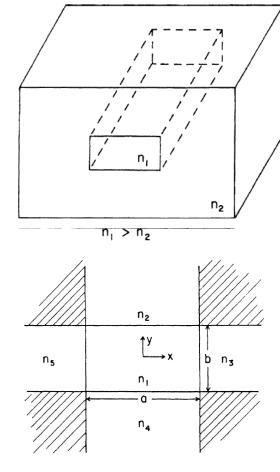
To simplify the analysis, we follow Marcatili's method (an approximate solution), assuming that all modes are well-guided, i.e., above the cutoff condition.

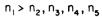
- The field magnitudes in the shaded corner regions are small enough to be neglected
- Field decays exponentially in Regions 2-5 with most of the power being confined to Region 1.

Since the index contrast exists in both the x and y directions, the electric field can be denoted as:

$$E^{x}_{pq}$$
 and E^{y}_{pq} , i.e. the electric field distributing along either x or y direction

where p and q represent the number of field nodes in the x and y directions, respectively.

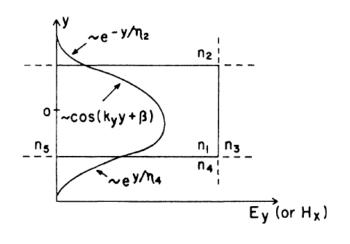


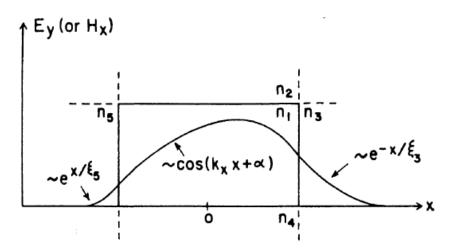


Modes in a Strip (rectangular) Waveguide

- For E_{pq}^{x} modes, dominate components are: E_{x} , H_{y}
- For E_{pq}^{y} modes, dominate components are: E_y , H_x

For example, the mode profile of E^{y}_{00} as:





Note that the shape of the mode is characterized by **extinction coefficients** η_2 , ξ_3 , η_4 , and ξ_5 in the regions where it is exponential, and by **propagation constants** k_x and k_y in *Region 1*



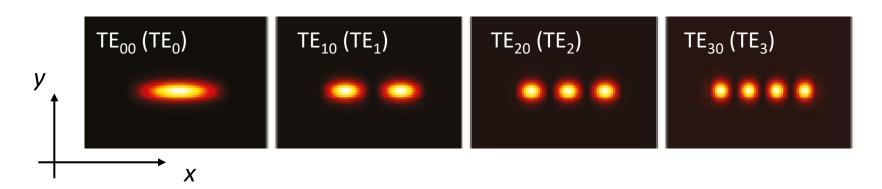
Modes in a Strip (rectangular) Waveguide

In practice, the width (x-direction) of a rectangular waveguide is usually larger than its height (y-direction), for example, a **500 nm** \times **220 nm** SOI waveguide.

In such cases:

- The refractive index contrast along **y-direction** is stronger, leading to **tighter confinement** and typically a **single-peaked field profile** without nodes (i.e., no oscillations along *y*).
- Along x-direction, the confinement is weaker, making it easier to form higher-order modes with multiple nodes/peaks.

Thus, the dominant field component is E_{pq}^{y} (p=0,1,2,3,... and q=0), and the supported modes are known as quasi-TE modes.



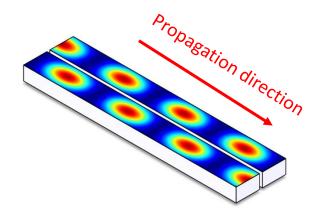


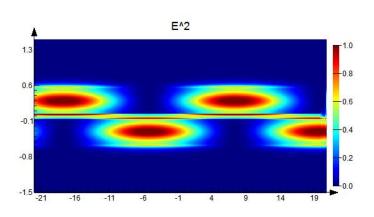
Basics of Mode Coupling

When two waveguides are brought close to each other, a phenomenon called **mode coupling** occurs, which means that optical energy periodically transfers between the two waveguides.

This happens because:

- The evanescent fields of the two waveguides extend into the surrounding space, and when placed close enough, they overlap and interact.
- This interaction enables **periodic energy transfer** between the two waveguides, where energy oscillates back and forth between the waveguides (like beating)







Basics of Mode Coupling

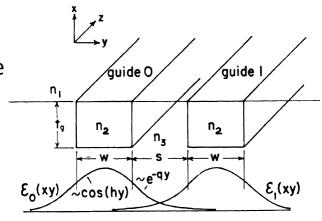
Coupled-Mode Theory of Synchronous Coupling

Coupling between two identical lossless waveguides ($\beta = \beta_0 = \beta_1$), and the field of the propagating mode is denoted, as:

$$\overline{E}(x, y, z) = A(z)\overline{E}(x, y)$$

where A(z) is the complex amplitude of the field, such that the mode power equals

$$P(z) = |A(z)|^2 = A(z)A^*(z)$$



The mode coupling can be described by the general **coupled mode equations** for the amplitudes of the two modes:

$$\begin{cases}
\frac{dA_0(z)}{dz} = -i\beta A_0(z) - i\kappa A_1(z) \\
\frac{dA_1(z)}{dz} = -i\beta A_1(z) - i\kappa A_0(z)
\end{cases} (1.11)$$

where β_0 and β_1 are the mode propagation constants, and κ is the **coupling coefficient** between modes, which quantifies the strength of interaction between the two waveguides: the larger κ , the faster the energy transfer between them.

Basics of Mode Coupling

Assume that the light is all within Waveguide 0 at the position z=0, we have:

$$A_0(0) = 1$$
 and $A_1(0) = 0$

Thus, the solutions of the coupled mode equations are:

$$\begin{cases}
\frac{dA_{0}(z)}{dz} = -i\beta A_{0}(z) - i\kappa A_{1}(z) \\
\frac{dA_{1}(z)}{dz} = -i\beta A_{1}(z) - i\kappa A_{0}(z)
\end{cases}$$

$$\begin{cases}
A_{0}(z) = \cos(\kappa z)e^{-i\beta z} \\
A_{1}(z) = -i\sin(\kappa z)e^{-i\beta z}
\end{cases}$$

$$\begin{cases}
P_{0}(z) = A_{0}(z)A_{0}^{*}(z) = \cos^{2}(\kappa z) \\
P_{1}(z) = A_{1}(z)A_{1}^{*}(z) = \sin^{2}(\kappa z)
\end{cases}$$

power flow in waveguides

It can be seen that the **coupling length** *L* necessary for complete transfer of power from one guide to the other is given by:

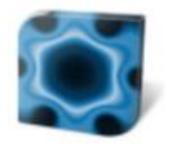
$$L = \frac{\pi}{2\kappa} + \frac{m\pi}{\kappa}$$
 where $m = 0,1,2,3...$

Simulation tools

Due to the complexity of mathematical models for optical waveguides, many computer programs and simulation tools have been developed to facilitate waveguide design and analysis.

Commercial software for waveguide mode analysis:





Ansys Lumerical FDTD/MODE

COMSOL Multiphysics (FEM)

In the following sessions, we will use **Lumerical** simulation tools (also **Matlab**-based numerical models) to perform calculations and simulations for optical waveguides and related photonic devices.



Report 1

- 1. Download and install MATLAB (please follow the instructions at https://help.eng.cam.ac.uk/software/matlab/).
- 2. Write a *MATLAB* Script to simulate the modes supported in a symmetric **Silicon-on-Isolator (SOI)** planar waveguide $(\lambda = 1550 \text{ nm})$ with varying core thicknesses using the cutoff condition (see Eq. 1.9).
- 3. Try different material systems, such as Si₃N₄ or LiNbO₃ and repeat the analysis. Compare material influence on mode support.
- 4. Also, change the operating wavelengths, e.g., repeat analysis at **1310 nm**, **1600 nm**, to see the dispersion effect. Note, do consider the **material dispersion**, i.e. the refractive index of materials themselves also dependence on wavelength

Summarize your findings in Report 1, including key figures (e.g., mode count vs. thickness) and critical discussion.

